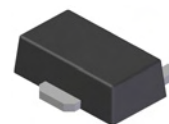


Features

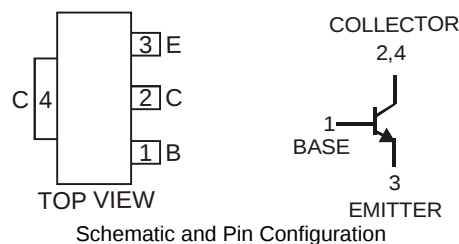
- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DPLS350Y)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**



SOT89-3L

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish — Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072 grams (approximate)



Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Collector Current	I_{CM}	5	A
Continuous Collector Current	I_C	3	A
Base Current	I_B	0.5	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ $T_A = 25^\circ\text{C}$	P_D	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	125	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)						
Collector-Base Cutoff Current	I _{CBO}	—	—	100	nA	V _{CB} = 50V, I _E = 0
Emitter-Base Cutoff Current	I _{EBO}	—	—	50	μA	V _{CB} = 50V, I _E = 0, T _A = 150°C
Collector-Emitter Cutoff Current	I _{CES}	—	—	100	nA	V _{CE} = 50V, V _{BE} = 0
Collector-Base Breakdown Voltage	V _{(BR)CBO}	50	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	50	—	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5	—	—	V	I _E = 100μA
ON CHARACTERISTICS (Note 4)						
DC Current Gain	h _{FE}	300	—	—	—	V _{CE} = 2V, I _C = 0.1A
		300	—	—		V _{CE} = 2V, I _C = 0.5A
		300	—	700		V _{CE} = 2V, I _C = 1A
		200	—	—		V _{CE} = 2V, I _C = 2A
		100	—	—		V _{CE} = 2V, I _C = 3A
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	38	80	mV	I _C = 0.5A, I _B = 50mA
		—	70	160		I _C = 1A, I _B = 50mA
		—	130	280		I _C = 2A, I _B = 100mA
		—	124	260		I _C = 2A, I _B = 200mA
		—	180	370		I _C = 3A, I _B = 300mA
Equivalent On-Resistance	R _{CE(SAT)}	—	62	130	mΩ	I _E = 2A, I _B = 200mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	—	1.1	V	I _C = 2A, I _B = 100mA
		—	—	1.2	V	I _C = 3A, I _B = 300mA
Base-Emitter Turn-on Voltage	V _{BE(ON)}	—	—	1.1	V	V _{CE} = 2V, I _C = 1A
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	100	—	—	MHz	V _{CE} = 5V, I _C = 100mA, f = 100MHz
Output Capacitance	C _{obo}	—	—	25	pF	V _{CB} = 10V, f = 1MHz

Notes: 4. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.

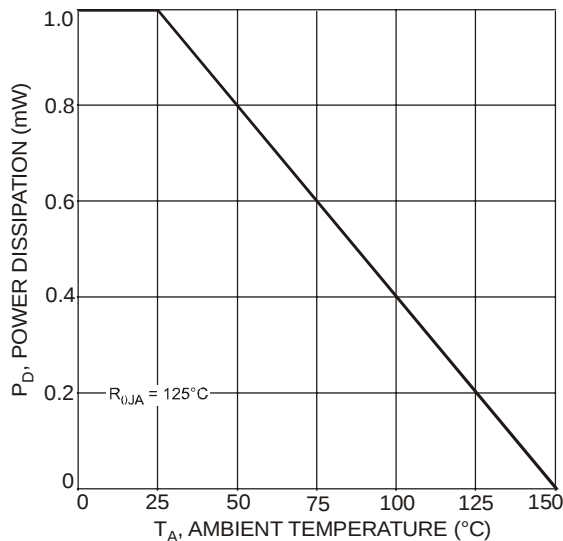


Fig. 1 Max Power Dissipation vs. Ambient Temperature

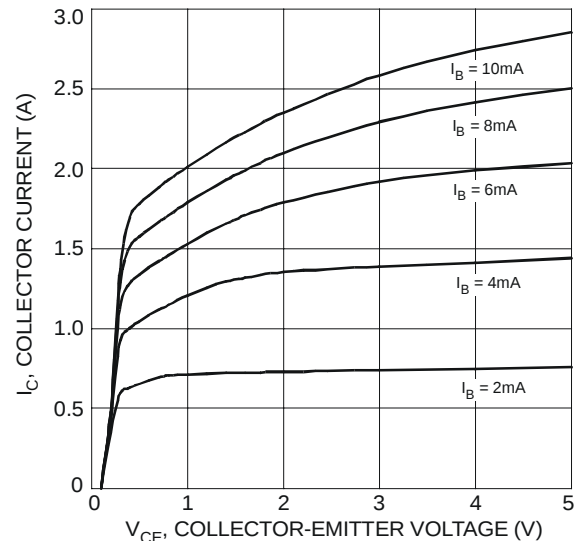


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

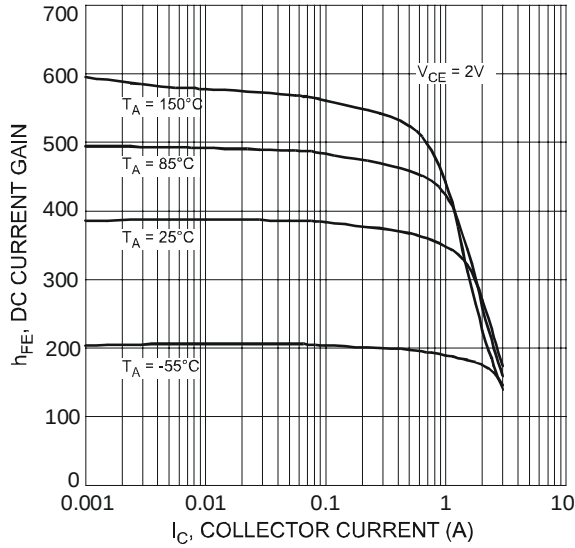


Fig. 3 Typical DC Current Gain vs. Collector Current

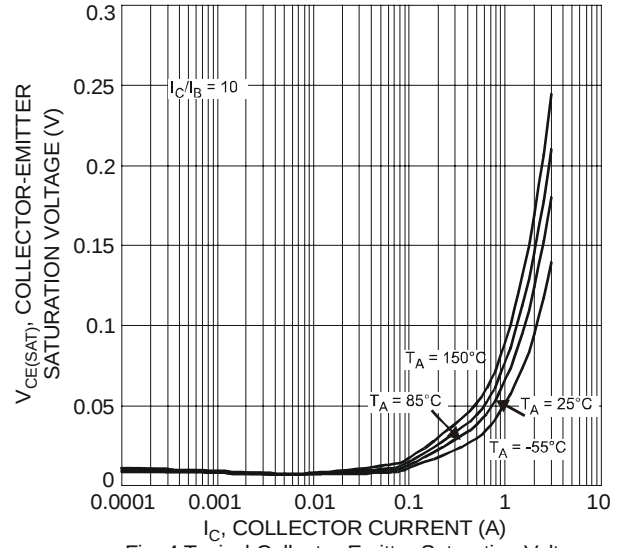


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

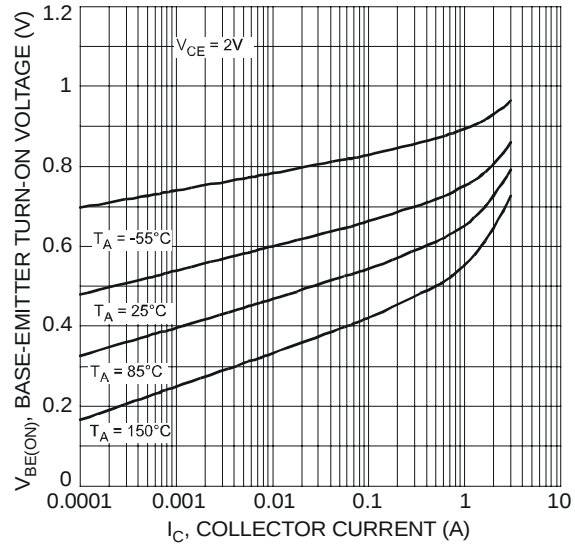


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

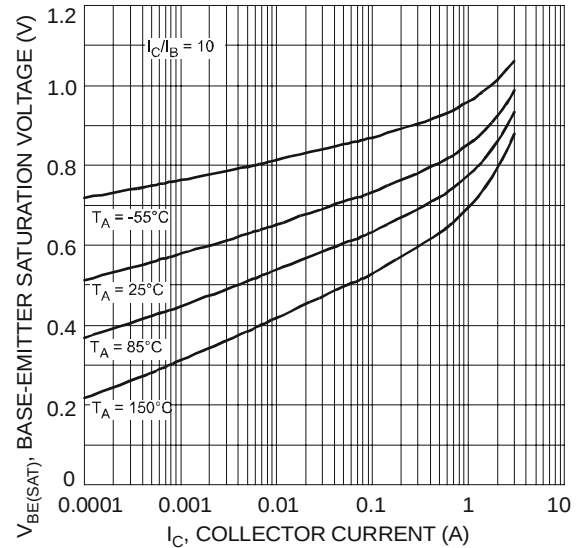


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

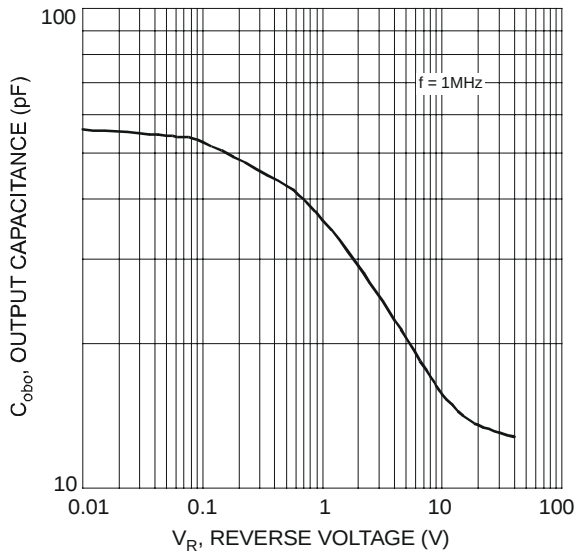


Fig. 7 Typical Output Capacitance Characteristics

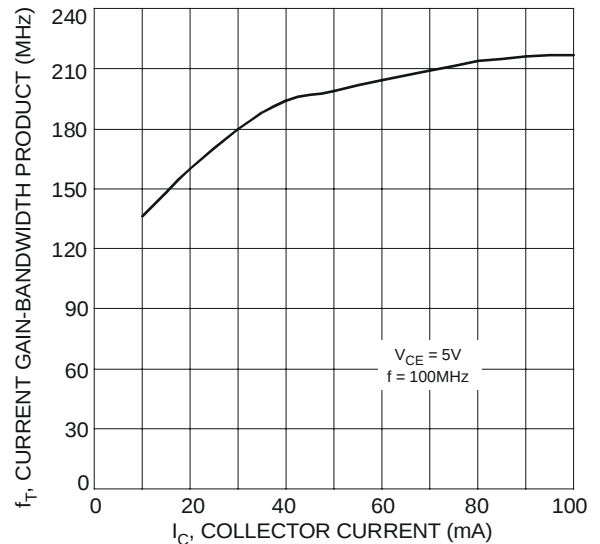


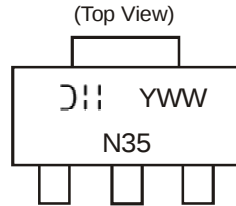
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DNLS350Y-13	SOT89-3L	2500/Tape & Reel

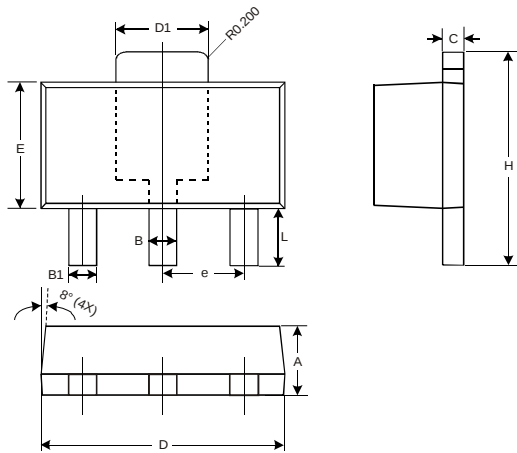
Notes: 5. For packaging details, go to our website at <http://www.diodes.com/ap02007.pdf>.

Marking Information



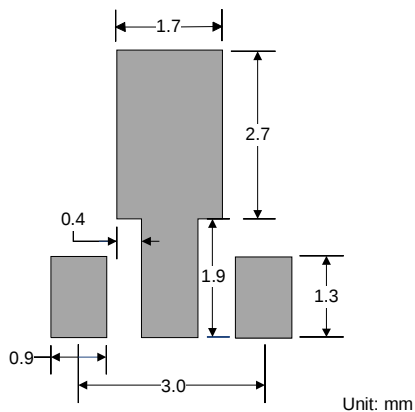
N35 = Product Type Marking Code
 YWW = Date Code Marking
 Y = Last digit of year ex: 7 = 2007
 WW = Week code 01 - 52

Package Outline Dimensions



SOT89-3L			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.45	0.55	0.50
B1	0.37	0.47	0.42
C	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.50	1.70	1.60
E	2.40	2.60	2.50
e	—	—	1.50
H	3.95	4.25	4.10
L	0.90	1.20	1.05
All Dimensions in mm			

Suggested Pad Layout



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<http://moschip.ru/get-element>

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